

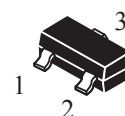
Surface Mount Switching Diode

(Pb) Lead(Pb)-Free

Features:

- *Low Current Leakage
- *Low Forward Voltage
- *Reverse Recover Time $T_{rr} \leq 6\text{ns}$
- *Small Outline Surface Mount SOT-23 Package

SWITCHING DIODE
200-215m AMPERRES
70-75 VOLTS

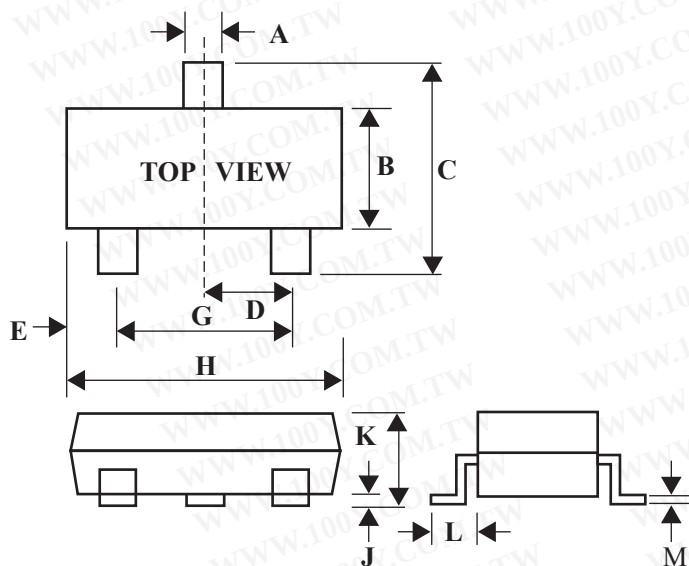


SOT-23

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

SOT-23 Outline Dimensions

Unit:mm



Dim	Min	Max
A	0.35	0.51
B	1.19	1.40
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.10
L	0.30	0.61
M	0.076	0.25

BAS16 / BAV70
BAW56 / BAV99



Maximum Ratings (EACH DIODE)

Characteristic	Symbol	BAS16	BAV70	BAW56	BAV99	Unit
Reverse Voltage	V _R	75	70			Volts
Forward Current	I _F	200			215	mAdc
Peak Forward Surge Current	I _{FM}	500				mAdc
Non-Repetitive Peak @ t=1.0us	I _{FSM}	2.0				Adc
Forward Surge Current @ t=1.0s		1.0				

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board *1, TA=25°C Derate Above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate*2 TA=25°C Derate Above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to + 150	°C

*1 ER-5=1.0x0.75x0.062 in

*2 Alumina=0.4x0.3x0.024 in 99.5% Alumina

Electrical Characteristics (TA=25°C Unless Otherwise Note) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
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Off Characteristics

Reverse Breakdown Voltage BAS16 (I _{BR} =100 μAdc) BAV70/BAW56/BAV99	V _{BR}	75 70		Vdc
Reverse Voltage Leakage Current V _R =75V BAS16 V _R =70V BAV70/BAW56/BAV99 V _R =25V, T _J =150°C BAS16/BAW56/BAV99 V _R =25V, T _J =150°C BAV70 V _R =75V, T _J =150°C BAS16 V _R =70V, T _J =150°C BAW56/BAV99 V _R =70V, T _J =150°C BAV70	I _R		1.0 2.5 30.0 60.0 50.0 50.0 100.0	μAdc

BAS16 / BAV70
BAW56 / BAV99



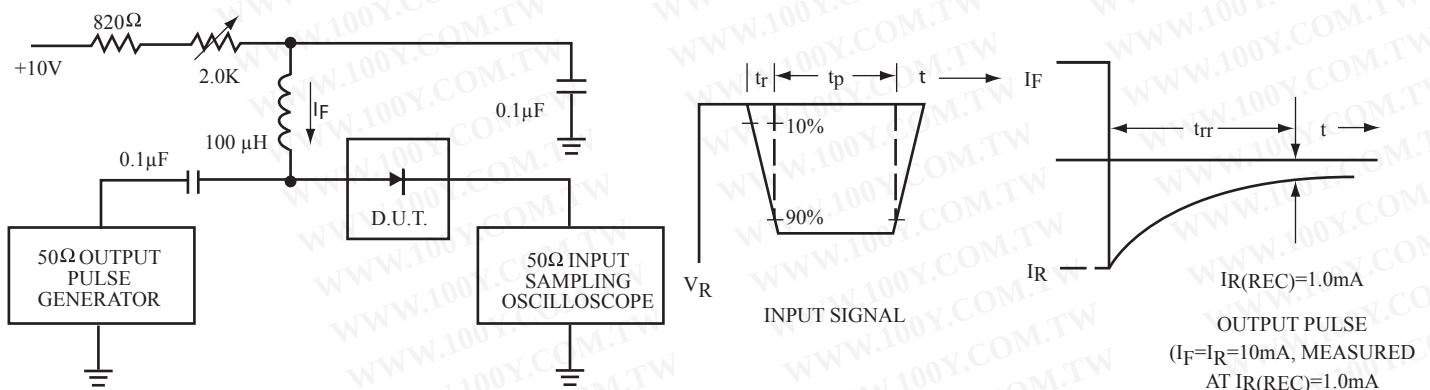
Off Characteristic

Characteristic	Symbol	Min	Max	Unit
Diode Capacitance (V _R =0, f=1.0MHz)	C _D		2.0 1.5	PF
Forward Voltage (I _F =1.0 mA _{dc}) (I _F =10 mA _{dc}) (I _F =50 mA _{dc}) (I _F =150 mA _{dc})	V _F		715 855 1000 1250	mV _{dc}
Reverse Recovery Time (Figure 1.) I _F =I _R =10 mA _{dc} , V _R =5.0V _{dc} I _R (REC)=1.0 mA _{dc} , R _L =100Ω	t _{rr}		6.0	nS

Device Marking

Item	Marking	Equivalent Circuit diagram
BAS16	A6	
BAV70	A4	
BAW56	A1	
BAV99	A7	

Figure 1. Recovery Time Equivalent Test Circuit



- Notes: 1. A 2.0 kΩ variable resistor for a Forward Current (I_F) of 10 mA
 2. Input pules is adjusted so I_R(peak) is equal to 10 mA
 3. t_p >> t_{rr}

FIGURE 2. FORWARD VOLTAGE

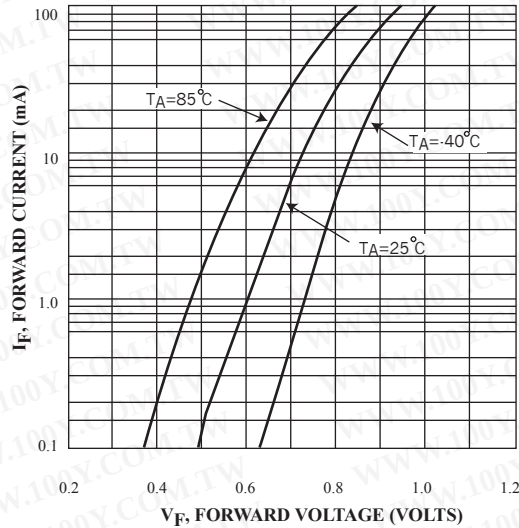


FIGURE 3. LEAKAGE CURRENT

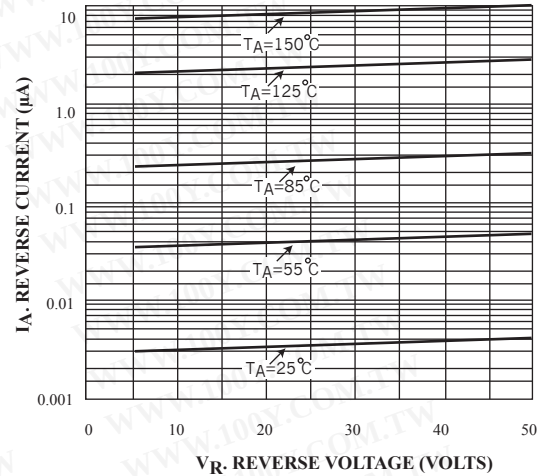


FIGURE 4. CAPACITANCE (BAS16)

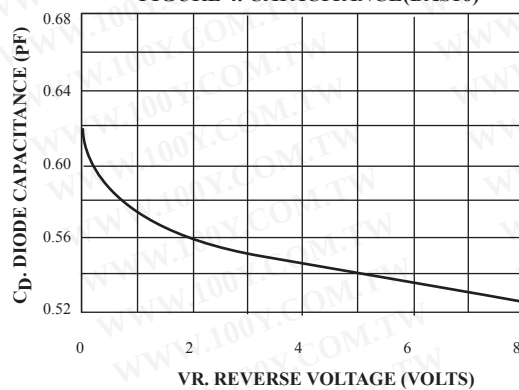


FIGURE 5. CAPACITANCE (BAV70)

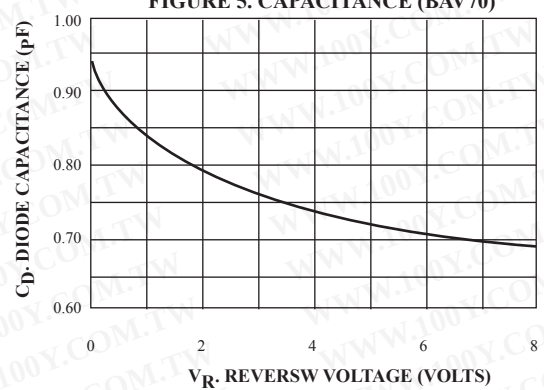


FIGURE 6. CAPACITANCE (BAW56)

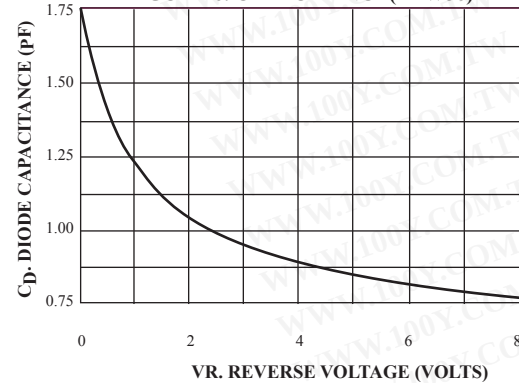


FIGURE 7. CAPACITANCE (BAV99)

